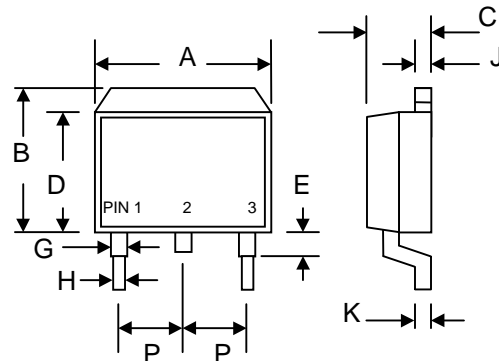


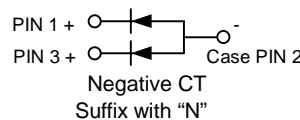
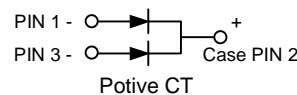
Features

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications



Mechanical Data

- Case: Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 1.7 grams (approx.)
- Mounting Position: Any
- Marking: Type Number
- Standard Packaging: 24mm Tape (EIA-481)



| D ² PAK/TO-263 | | |
|---------------------------|------|------|
| Dim | Min | Max |
| A | 9.8 | 10.4 |
| B | 9.6 | 10.6 |
| C | 4.4 | 4.8 |
| D | 8.5 | 9.1 |
| E | — | 0.7 |
| G | 1.0 | 1.4 |
| H | — | 0.9 |
| J | 1.2 | 1.4 |
| K | 0.3 | 0.7 |
| P | 2.35 | 2.75 |
| All Dimensions in mm | | |

Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

| Characteristic | Symbol | SB 820D | SB 830D | SB 840D | SB 850D | SB 860D | SB 880D | SB 8100D | Unit |
|---|--|-------------|---------|---------|---------|---------|---------|----------|------|
| Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage | V _{RRM} V _{RWM} V _R | 20 | 30 | 40 | 50 | 60 | 80 | 100 | V |
| RMS Reverse Voltage | V _{R(RMS)} | 14 | 21 | 28 | 35 | 42 | 56 | 70 | V |
| Average Rectified Output Current @T _C = 100°C | I _O | 8.0 | | | | | | | A |
| Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method) | I _{FSM} | 150 | | | | | | | A |
| Forward Voltage @I _F = 8.0A | V _{FM} | 0.55 | | 0.75 | | 0.85 | | | V |
| Peak Reverse Current @T _A = 25°C At Rated DC Blocking Voltage @T _A = 100°C | I _{RM} | 0.5 50 | | | | | | | mA |
| Typical Junction Capacitance (Note 1) | C _j | 400 | | | | | | | pF |
| Typical Thermal Resistance Junction to Ambient | R _{θJA} | 60 | | | | | | | K/W |
| Operating and Storage Temperature Range | T _j , T _{STG} | -50 to +150 | | | | | | | °C |

Note: 1. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.

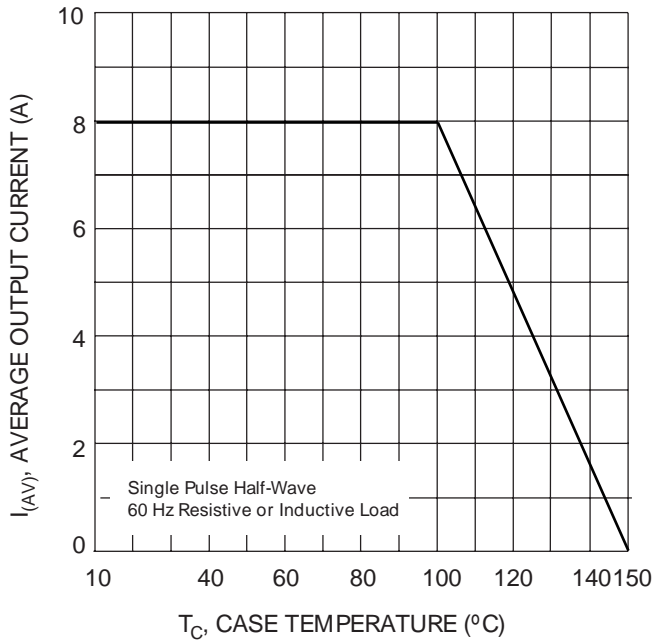


Fig. 1 Forward Current Derating Curve

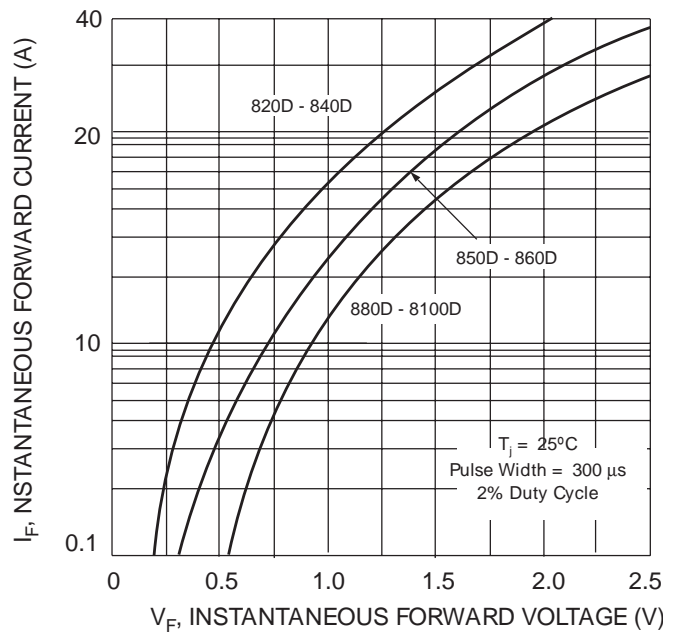


Fig. 2 Typical Forward Characteristics

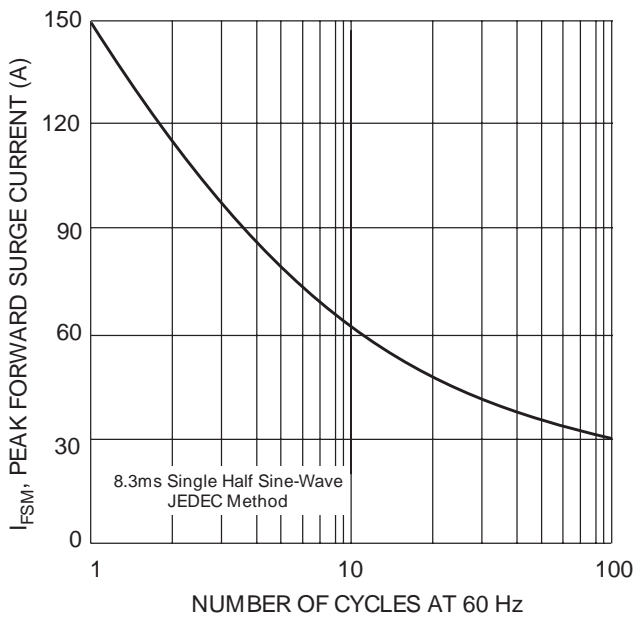


Fig. 3 Maximum Non-Repetitive Peak Fwd Surge Current

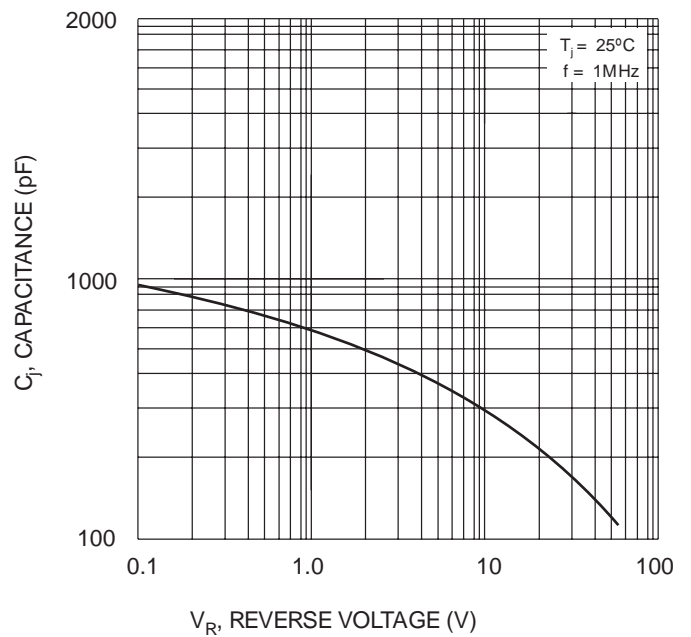


Fig. 4 Typical Junction Capacitance